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(73) Patent Right Holder: 000226057

Nichia Corporation

491-100 Oka, Kaminaka-Cho, Anan-Shi, Tokushima

(72) Inventor: Yoshiaki Tadatsu

c/o Nichia Corporation

491-100 Oka, Kaminaka-Cho, Anan-Shi, Tokushima

(72) Inventor: Shuji Nakamura

c/o Nichia Corporation

491-100 Oka, Kaminaka-Cho, Anan-Shi, Tokushima

(74) Agent: Patent Attorney: Yasuhiro Toyosu

Examiner Mitsuhiko Yoshino

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(54) [Invention Title] Light Emitting Diode

(57) [What is Claimed is:]

[Claim 1] A light emitting diode with a light emitting device (11) on a metal piece, whereas a fluorescent dye or pigment, which is excited with light from the light emitting device (11) and which emits fluorescent light

with wavelengths different from those of the excitation light, is added to a resin mold which surrounds the entirety of the light emitting device (11),

wherein

said fluorescent dye or pigment (5) is excited with the visible light from the light emitting device, and emits visible light with a longer wavelength than that of the excitation light;

said light emitting device is equipped with n-type and p-type gallium nitride related compound semiconductor layers which are stacked on a sapphire substrate and which emit blue visible light and;

the light emitting device (11) which is made of gallium nitride related compound semiconductors is equipped with a pair of electrodes on the same surface of the device which is located on an opposite side of a surface of the device which comes in contact with the metal piece, the electrodes being wire-bonded with gold wires, whereas one of the electrodes is an ohmic electrode which is connected to a section where a surface of the n-type gallium nitride related compound semiconductor is exposed.

[Detailed Explanation of Invention]

[Technological Field]

[0001]

The present invention relates to a light emitting diode (hereafter referred to as an LED) in which a light emitting device is surrounded with a resin mold.

[0002]

[Conventional Technologies]

In general, an LED has a structure as illustrated in Figure 1. The numeral designator 1 represents a light emitting device which is cut to a piece of 1mm square or smaller and which is made of materials such as GaAlAs and GaP, the numeral designator 2 represents a metal stem, the numeral designator 3 represents a metal post and the numeral designator 4 represents a resin mold which surrounds the light emitting device. The back surface electrode of the light emitting device 1 is attached on the metal stem 2 using a material such as silver paste, thereby electrically connecting it thereto. A gold wire coming from the metal post 3, which is the other electrode, is bonded to the surface of the front surface electrode of the light emitting device 1. Further, the light emitting device 1 is molded using the transparent resin mold 4.

[0003]

Ordinarily, a resin with a large index of refraction and a high transparency is selected for the resin mold 4, so that the emission light from the light emitting device is efficiently emitted to the air. In other cases, an inorganic or organic pigment is mixed as a coloring agent in the resin mold 4 in order to convert or correct the emission color of the light emitting device.

[0004]

[Issues to be Resolved by Invention]

Conventionally, however, most of technologies to convert the wavelength by adding a coloring agent to a resin mold are not put into practical use and only handful technologies to employ a coloring agent for color correction are utilized. This is because adding an enough amount of a coloring agent, which is a non-light-emission material, to realize the wavelength conversion greatly reduces the brightness of an LED.

[0005]

In addition, currently realized LED's are infrared, red, yellow and green light emitting ones. Blue and ultraviolet LED's are not yet realized. Research is being conducting with semiconductors such as ZnSe which is a II-VI group material, SiC which is a IV-IV group material, and GaN which is a III-V group material. Recently, among these materials, gallium nitride related compound semiconductors which are expressed with a general formula of  $Ga_xAl_{1-x}N$  (where  $0 \leq x \leq 1$ ) are attracting attentions because it was found that they exhibit relatively superior light emission at normal temperatures. Moreover, LED's employing gallium nitride related compound semiconductors in which a pn junction was realized for the first time were reported (Oyo Butsuri, vol. 60, No. 2, pp163-166, 1991). According to this publication, LED's employing gallium nitride related compound semiconductors have a main emission peak at around 430nm and also have another emission peak in the ultraviolet range of around 370nm. These wavelengths are the shortest among those for the above semiconductor materials. Such LED's, however, have a disadvantage in that their luminosity factor is poor because the emission color is close to violet, as their emission wavelength indicates.

[0006]

The present invention was conceived with considerations being given to such circumstances. Its purpose is to improve the luminosity factor and brightness of LED's having a light emission device which is made of gallium nitride related compound semiconductors.

[Means to Resolve Issues]

[0007]

A light emitting diode of the present invention has a light emitting device 11 and a fluorescent dye or pigment 5 which is excited with light from the light emitting device 11 and which emits fluorescent light with wavelengths longer than those of the excitation light. Further, in the light emitting diode of the present invention, the fluorescent dye or pigment 5 is arranged so as to surround the light emitting device 11 on a metal piece, and the light emitting device is equipped with stacked n-type and p-type gallium nitride related compound semiconductors which emit blue visible light. The light emitting device 11 which is made of gallium nitride related compound semiconductors is equipped with a pair of electrodes on the same surface of the device which is located on an opposite side of a surface of the device which comes in contact with the metal piece, the

electrodes being wire-bonded with gold wires. One of the electrodes is an ohmic electrode which is connected to a section where a surface of the n-type gallium nitride related compound semiconductor is exposed.

[0008]

#### [Embodiment to Implement Invention]

Figure 2 illustrate an example to depict the structure of an LED according to the present invention. The numeral designator 11 represents a blue light emitting device in which n-type and p-type GaAlN layers are stacked on a sapphire substrate, the numeral designators 2 and 3 represent a metal stem and a metal post, respectively, in the same manner as in Figure 1, and the numeral designator 4 represents a resin mold surrounding the light emitting device. There is the sapphire insulating substrate on the back surface of the light emitting device 11 and an electrode can not be made on the back surface. Therefore, in order to electrically connect an n-electrode on the GaAlN layer to the metal stem 2, a method is employed in which the GaAlN layers are etched to expose the surface of the n-type layer, upon which an ohmic electrode is attached. The ohmic electrode and the metal stem 2 are electrically connected using a gold wire. Moreover, the other electrode is wire-bonded to the surface of the p-type layer using a gold wire coming from the metal post 3 in the same manner as in Figure 1. Further, a fluorescent dye 5 which is excited with light with a wavelength near 420 to 440nm and which emits light with an emission peak near 480nm is added to the resin mold 4.

[0009]

#### [Advantages of Invention]

A fluorescent dye or pigment in a light emitting diode of the present invention is excited with visible light and emits light with a longer wavelength than that of the excitation light. Contrarily, there are fluorescent pigments which are excited with a long-wavelength light and which emit light with a shorter wavelength than that of the excitation light. Such materials, however, have a very poor energy efficiency and provides a very weak emission light. As discussed above, gallium nitride related compound semiconductors have emission peaks in the shortest wavelength range among semiconductor materials which are employed for LED's. Moreover, they have an emission peak in the ultraviolet range. Therefore, when they are employed as materials for a light emitting device and when a fluorescent dye or pigment is added to a resin mold surrounding the light emitting device, the fluorescent material can be most optimally excited. Therefore, different types of a fluorescent dye or pigment can not only correct color of blue LED's but also convert light into a variety of wavelengths. Further, visible light is converted to one with a longer wavelength with a good energy efficiency and hence, the amount of a fluorescent dye or pigment can be small and the invention is very excellent from the view point of reducing the degradation of luminosity factor.

#### [Brief Explanation of Figures]

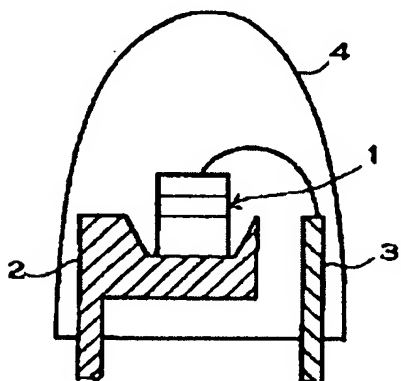
[Figure 1] A schematic cross section to illustrate the structure of a conventional LED.

[Figure 2] A schematic cross section to illustrate the structure of an example of an LED according to the present invention.

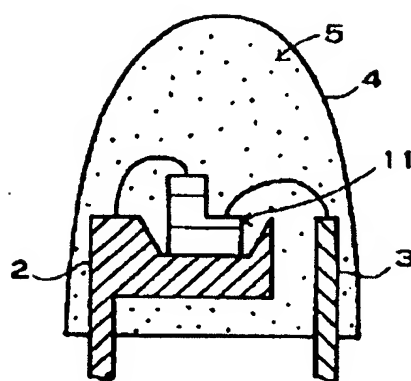
[Explanation of Numeral Designators]

- 11 Light emitting device
- 2 Metal stem
- 3 Metal post
- 4 Resin mold
- 5 Fluorescent dye

[Figure 1]



[Figure 2]



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- (56) References: Patent Application Publication H01-179471 (JP, A)  
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